

ABSTRACT OF THE DISCLOSURE

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There is provided, according to one embodiment of this invention, a semiconductor memory device ~~comprising~~ ^{including} first memory elements to store a first state or a second state according to a change in resistance value, each of the first memory elements ~~comprising~~ ^{including} one terminal and the other terminal, the first memory elements arranged parallel with each other, a first wiring connected with the one terminal of each of the first memory elements, and a second wiring formed in parallel with the first wiring and connected with the other terminal of each of the first memory elements, wherein the first state or the second state stored in one of selected from the first memory elements is read out by delivering an electric current from one of the first and second wirings via the one of selected from the first memory elements to the other of the first and second wirings.

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